# DACO SEMICONDUCTOR CO.,LTD.

MBRA80020CT(R)
THRU
MBRA800100CT(R)

## SCHOTTKY DIODE MODULE TYPES 800A

## Features

High surge Capability
Types Up to 100V $V_{RRM}$

**HEAVY TWIN TOWER**

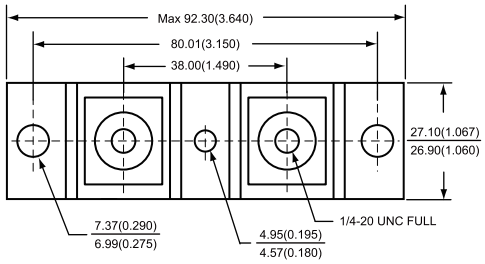
## Maximum Ratings

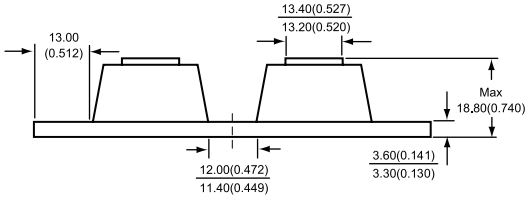
Operating Temperature: -55℃ to+150 ℃

Storage Temperature: -55℃ to+150 ℃

| Part Number | Maximum Recurrent Peak Reverse Voltage | Maximum RMS Voltage | Maximum DC Blocking Voltage |
|---|---|---|---|
| MBRA80020CT(R) | 20V | 14V | 20V |
| MBRA80030CT(R) | 30V | 21V | 30V |
| MBRA80035CT(R) | 35V | 25V | 35V |
| MBRA80040CT(R) | 40V | 28V | 40V |
| MBRA80045CT(R) | 45V | 32V | 45V |
| MBRA80060CT(R) | 60V | 42V | 60V |
| MBRA80080CT(R) | 80V | 56V | 80V |
| MBRA800100CT(R) | 100V | 70V | 100V |

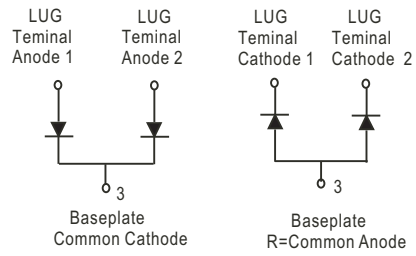
Dimensions in mm (1 mm = 0.0394")




## Electrcal Characteristics @ 25℃ Unless Otherwise Specified

| | | | |
|---|---|---|---|
| Average Forward Current (Per pkg) | $I_{F(AV)}$ | 800A | $T_C$ =100 ℃ |
| Peak Forward Surge Current (Per leg) | $I_{FSM}$ | 6000A | 8.3ms , half sine |
| Maximum Instantaneous Forward Voltage (Per leg) 20V~45V<br>50V~60V<br>80V~100V | $V_F$ | 0.72V<br>0.78V<br>0.84V | IFM=400A;TJ=25℃ |
| Maximum Instantaneous Reverse Current At Rated DC Blocking Voltage (Per leg) NOTE (1) | $I_R$ | 1 mA<br>10 mA<br>50 mA | $T_J$ = 25 ℃<br>$T_J$ =100 ℃<br>$T_J$ =150 ℃ |
| Maximum Thermal Resistance Junction To Case (Per leg) | $R_{\theta jc}$ | 0.25℃/W | |




NOTE :
(1) Pulse Test: Pulse Width 300 $\mu$ sec,Duty<2%

Figure.1-Typical Forward Characteristics

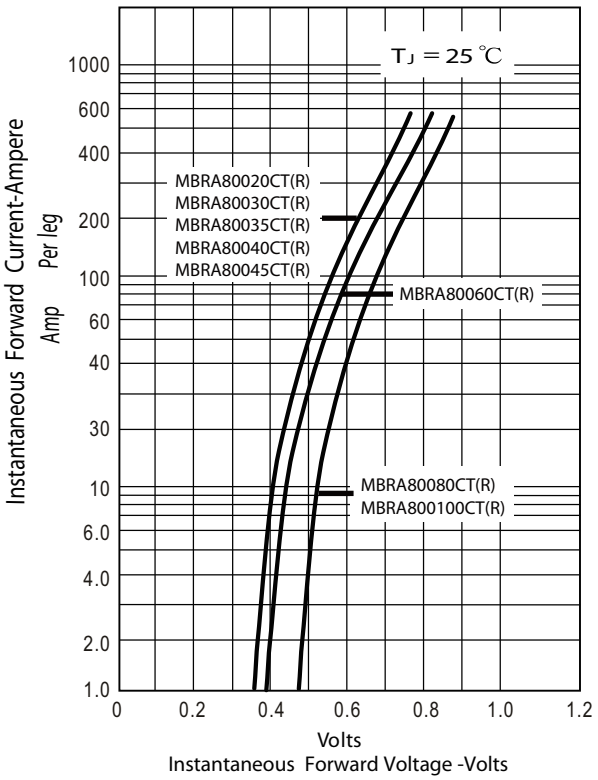
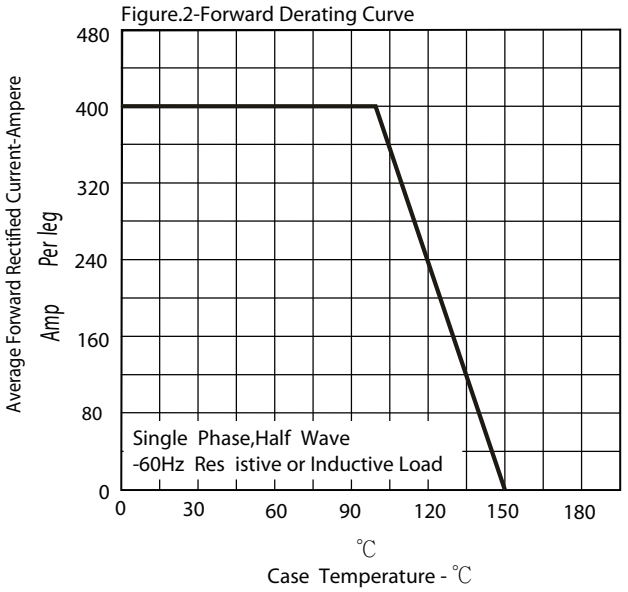



Figure.2-Forward Derating Curve




Figupre.3-Peak Forward Surge Current

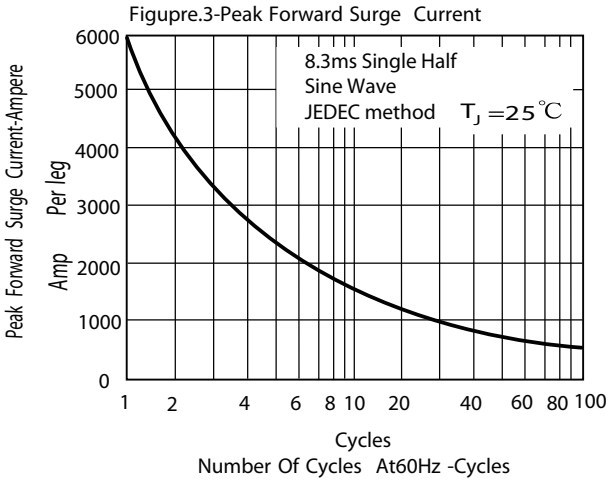



Figure.4-Typical Reverse Characteristics